

MOS FIELD EFFECT TRANSISTOR 2SK4069

SWITCHING N-CHANNEL POWER MOSFET

DESCRIPTION

The 2SK4069 is N-channel MOS FET device that features a low on-state resistance and excellent switching characteristics, and designed for low voltage high current applications such as DC/DC converter with synchronous rectifier.

FEATURES

- Low on-state resistance
 $R_{DS(on)1} = 12 \text{ m}\Omega \text{ MAX.}$ ($V_{GS} = 10 \text{ V}$, $I_D = 15 \text{ A}$)
- Low Q_{GD} : $Q_{GD} = 3.2 \text{ nC TYP.}$
- 4.5 V drive available

ORDERING INFORMATION

PART NUMBER	PACKAGE
2SK4069(1)-S27-AY ^{Note}	TO-251 (MP-3-b)
2SK4069-ZK-E1-AY ^{Note}	TO-252 (MP-3ZK)
2SK4069-ZK-E2-AY ^{Note}	TO-252 (MP-3ZK)

Note Pb-free (This product does not contain Pb in external electrode.)

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$)

Drain to Source Voltage ($V_{GS} = 0 \text{ V}$)	V_{DSS}	25	V
Gate to Source Voltage ($V_{DS} = 0 \text{ V}$)	V_{GSS}	± 20	V
Drain Current (DC) ($T_C = 25^\circ\text{C}$)	$I_{D(DC)}$	± 30	A
Drain Current (pulse) ^{Note1}	$I_{D(pulse)}$	± 120	A
Total Power Dissipation ($T_C = 25^\circ\text{C}$)	P_{T1}	21	W
Total Power Dissipation	P_{T2}	1.0	W
Channel Temperature	T_{ch}	150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-55 to +150	$^\circ\text{C}$
Single Avalanche Current ^{Note2}	I_{AS}	18	A
Single Avalanche Energy ^{Note2}	E_{AS}	32.4	mJ

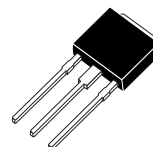
Notes 1. $PW \leq 10 \mu\text{s}$, Duty Cycle $\leq 1\%$

2. Starting $T_{ch} = 25^\circ\text{C}$, $V_{DD} = 12 \text{ V}$, $R_G = 25 \Omega$, $V_{GS} = 20 \rightarrow 0 \text{ V}$, $L = 100 \mu\text{H}$

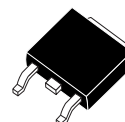
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(TO-251)



(TO-252)

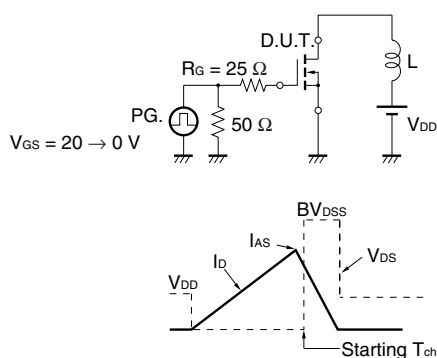


ELECTRICAL CHARACTERISTICS (T_A = 25°C)

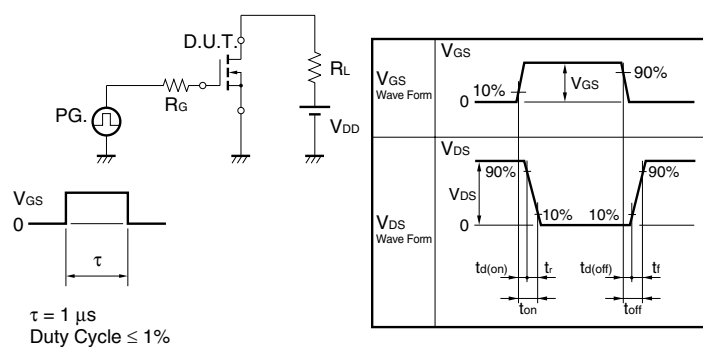
CHARACTERISTICS	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 25 V, V _{GS} = 0 V			10	μA
Gate Leakage Current	I _{GSS}	V _{GS} = ±20 V, V _{DS} = 0 V			±100	nA
Gate Cut-off Voltage	V _{GS(off)}	V _{DS} = 10 V, I _D = 1 mA	1.5	2.0	2.5	V
Forward Transfer Admittance Note	y _{fs}	V _{DS} = 10 V, I _D = 7.5 A	5	10		S
Drain to Source On-state Resistance Note	R _{DS(on)1}	V _{GS} = 10 V, I _D = 15 A		9.4	12	mΩ
	R _{DS(on)2}	V _{GS} = 4.5 V, I _D = 15 A		15	21	mΩ
Input Capacitance	C _{iss}	V _{DS} = 10 V		860		pF
Output Capacitance	C _{oss}	V _{GS} = 0 V		255		pF
Reverse Transfer Capacitance	C _{rss}	f = 1 MHz		90		pF
Turn-on Delay Time	t _{d(on)}	V _{DD} = 12 V, I _D = 30 A		14/7.5		ns
Rise Time	t _r	V _{GS} = 4.5 V/12 V		13/4.2		ns
Turn-off Delay Time	t _{d(off)}	R _G = 3 Ω		1.9/24		ns
Fall Time	t _f			14/4.4		ns
Total Gate Charge	Q _{G1}	V _{DD} = 12 V, V _{GS} = 12 V, I _D = 30 A		17		nC
Total Gate Charge	Q _{G2}	V _{DD} = 12 V, V _{GS} = 4.5 V, I _D = 30 A		6.7		nC
Gate to Source Charge	Q _{GS}	V _{DD} = 12 V, I _D = 30 A		2.4		nC
Gate to Drain Charge	Q _{GD}			3.2		nC
Gate Resistance	R _G			1.5		Ω
Body Diode Forward Voltage Note	V _{F(S-D)}	I _F = 30 A, V _{GS} = 0 V		0.9	1.5	V
Reverse Recovery Time	t _{rr}	I _F = 30 A, V _{GS} = 0 V		29		ns
Reverse Recovery Charge	Q _{rr}	di/dt = 100 A/μs		20		nC

Note Pulsed

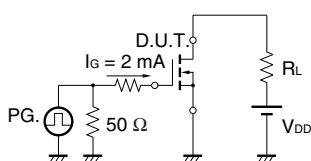
TEST CIRCUIT 1 AVALANCHE CAPABILITY



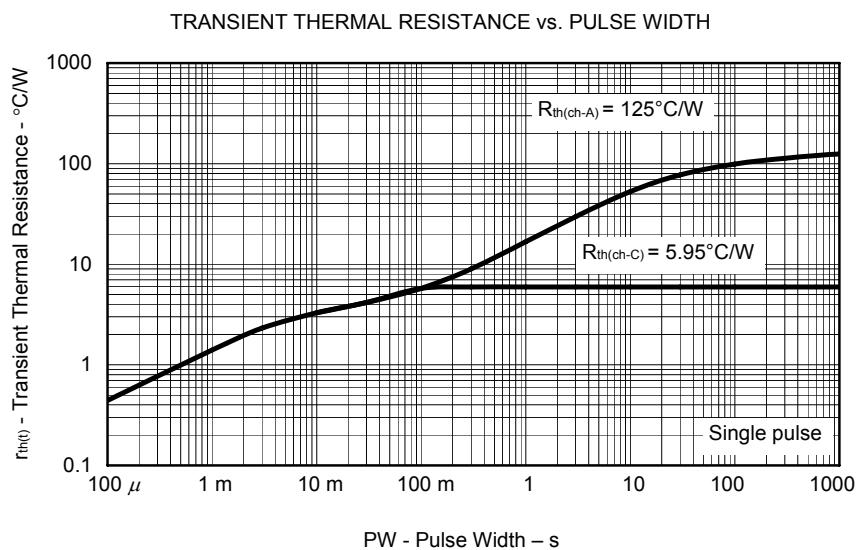
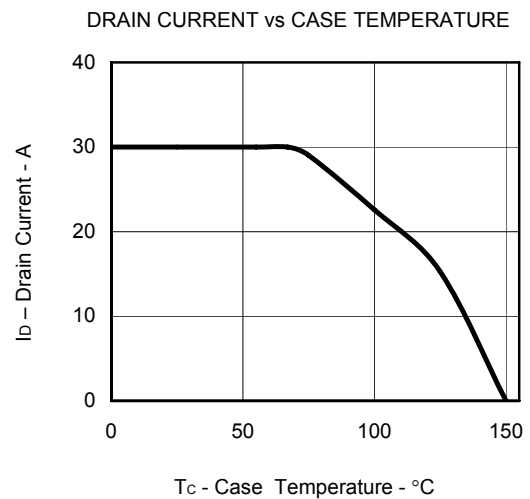
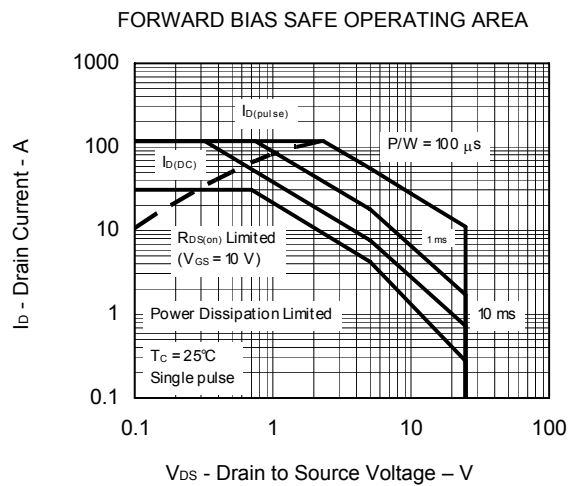
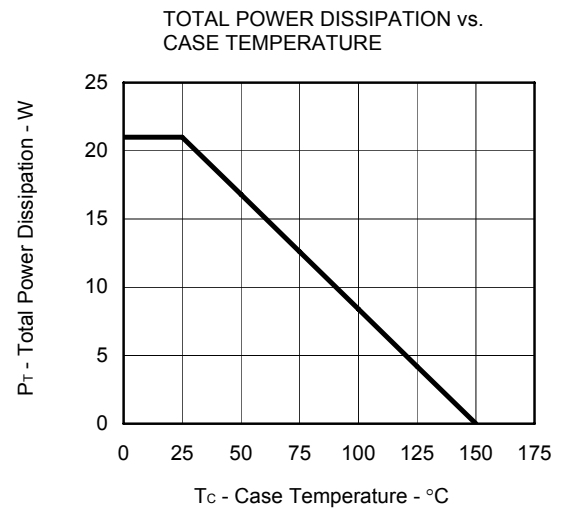
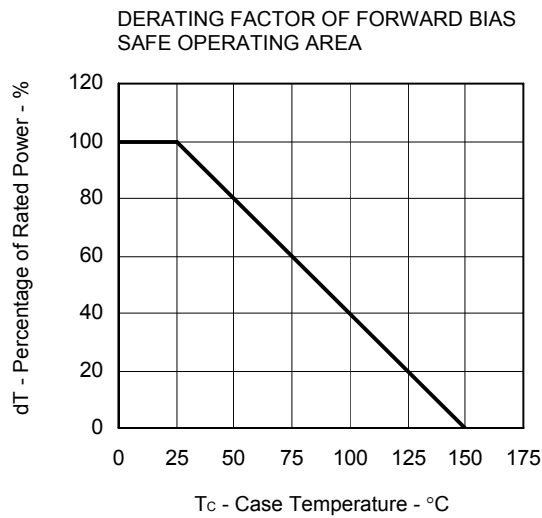
TEST CIRCUIT 2 SWITCHING TIME



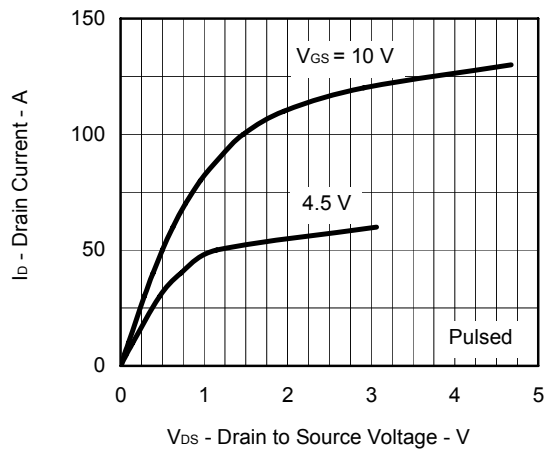
TEST CIRCUIT 3 GATE CHARGE



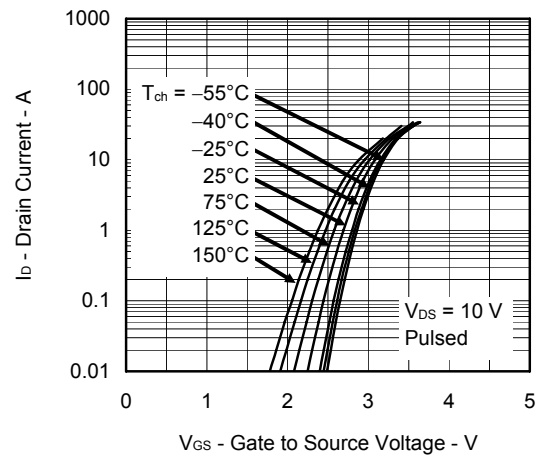
TYPICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$)



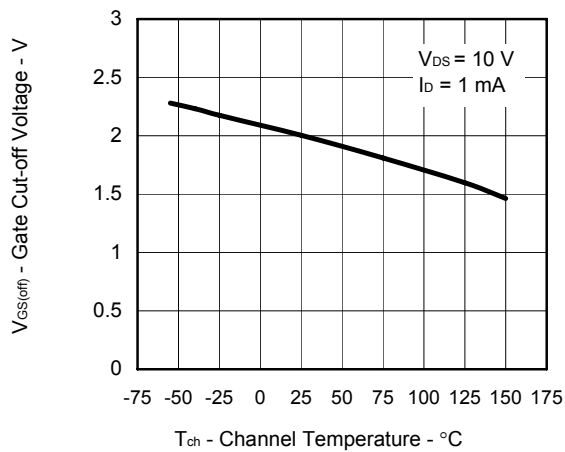
DRAIN CURRENT vs.
DRAIN TO SOURCE VOLTAGE



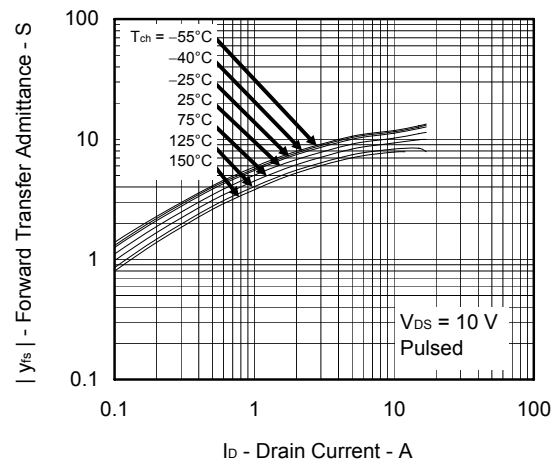
FORWARD TRANSFER CHARACTERISTICS



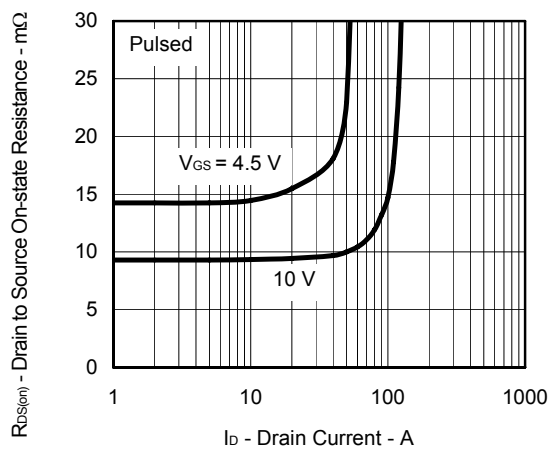
GATE CUT-OFF VOLTAGE vs.
CHANNEL TEMPERATURE



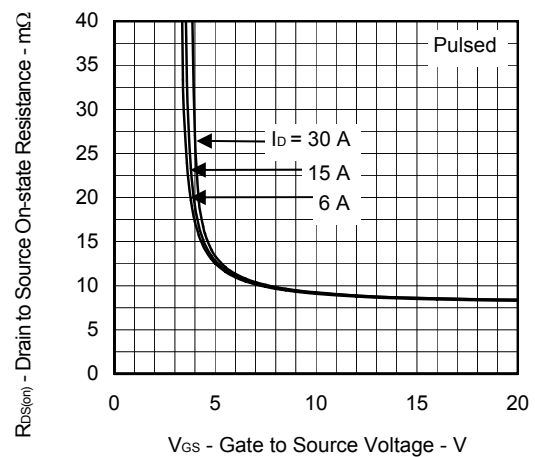
FORWARD TRANSFER ADMITTANCE vs.
DRAIN CURRENT

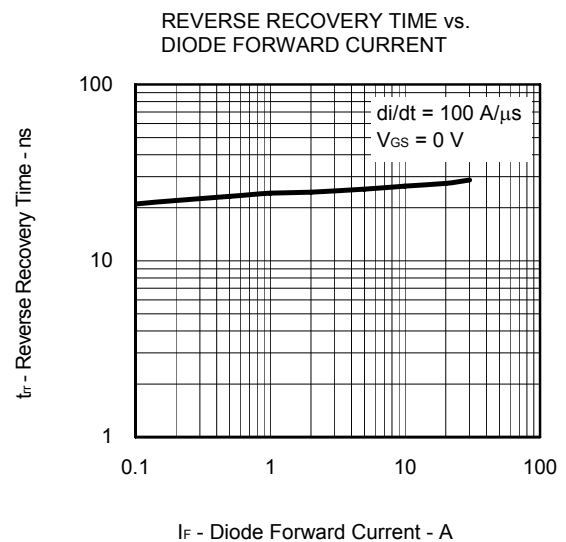
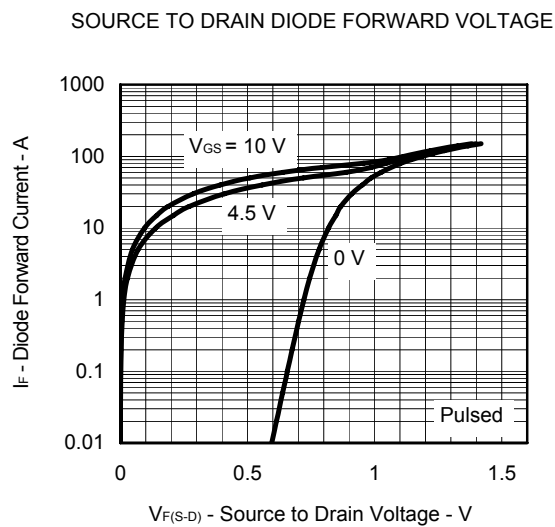
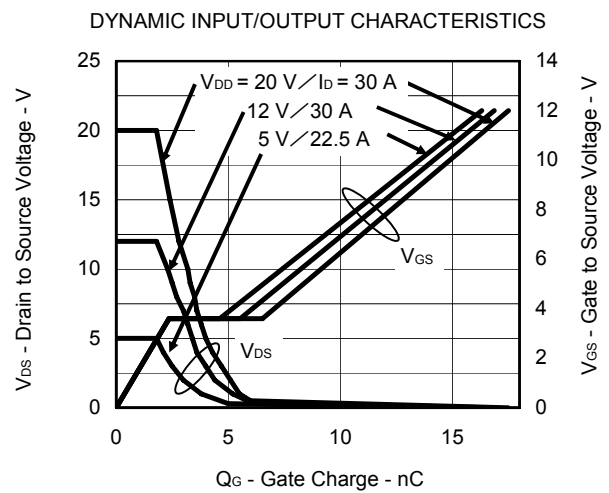
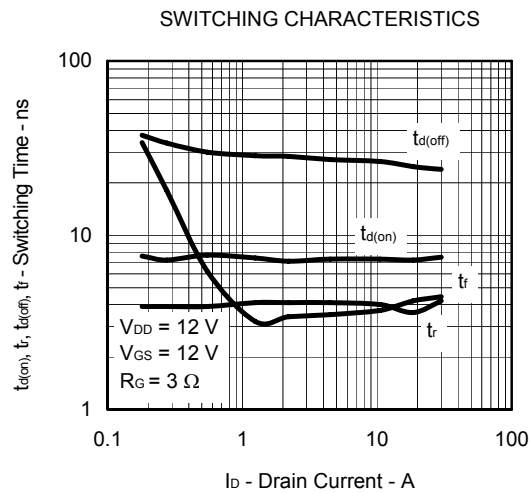
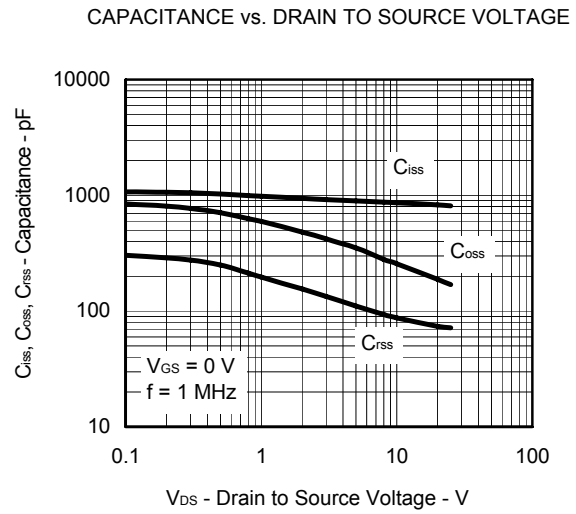
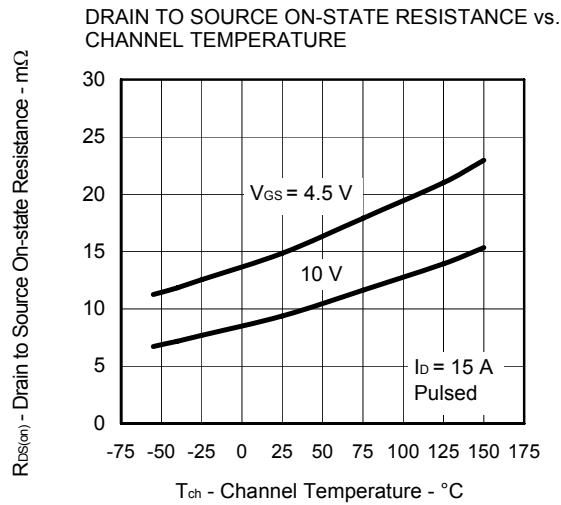


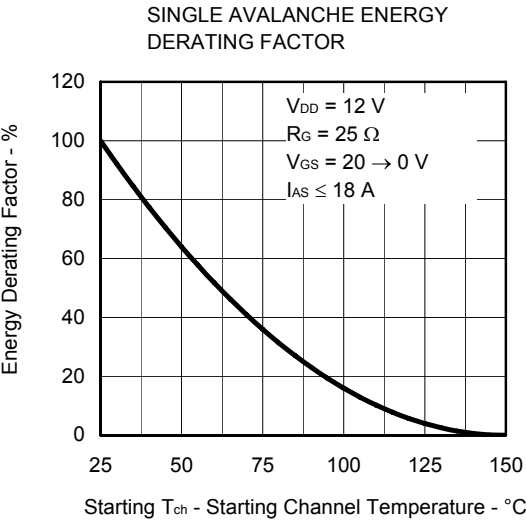
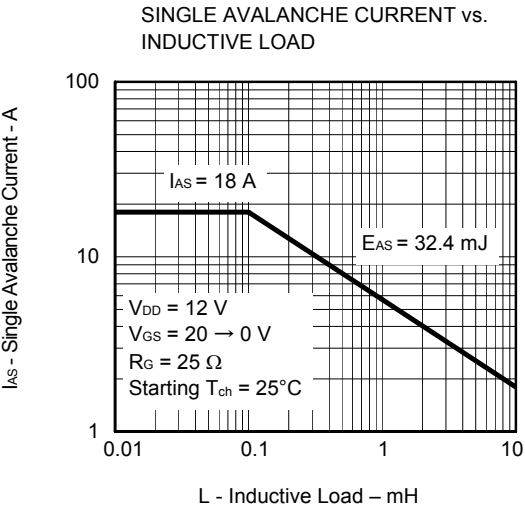
DRAIN TO SOURCE ON-STATE RESISTANCE vs.
DRAIN CURRENT



DRAIN TO SOURCE ON-STATE RESISTANCE vs.
GATE TO SOURCE VOLTAGE



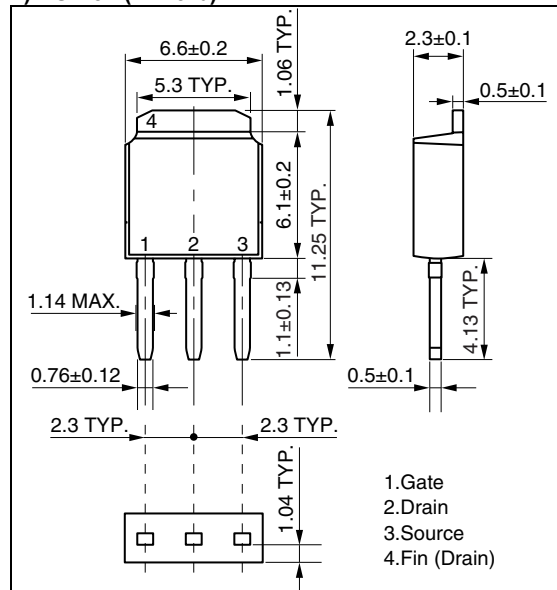




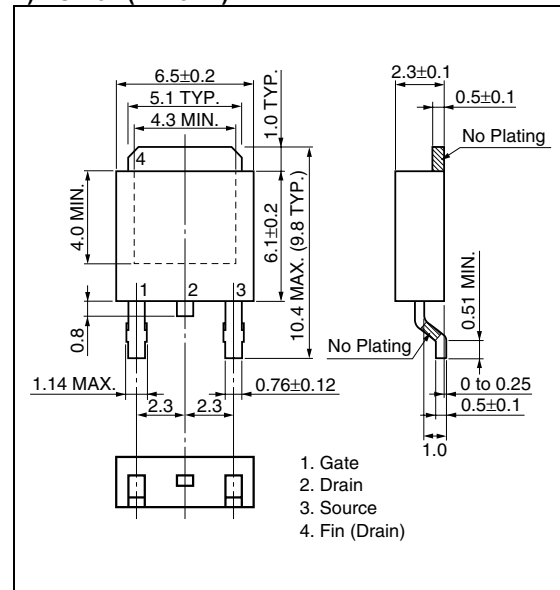
PACKAGE DRAWINGS (Unit: mm)

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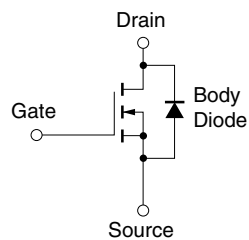
1) TO-251 (MP-3-b)



2) TO-252 (MP-3ZK)



EQUIVALENT CIRCUIT



Remark Strong electric field, when exposed to this device, can cause destruction of the gate oxide and ultimately degrade the device operation. Steps must be taken to stop generation of static electricity as much as possible, and quickly dissipate it once, when it has occurred.

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